

# P-Channel Enhancement Mode Vertical DMOS FETs

#### **Features**

- ► Low threshold (-2.4V max.)
- ▶ High input impedance
- ► Low input capacitance (125pF max.)
- Fast switching speeds
- Low on-resistance
- ▶ Free from secondary breakdown
- Low input and output leakage
- Complementary N and P-channel devices

#### **Applications**

- Logic level interfaces ideal for TTL and CMOS
- Solid state relays
- ▶ Battery operated systems
- Photo voltaic drives
- Analog switches
- General purpose line drivers
- Telecom switches

#### **General Description**

This low threshold enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

#### **Ordering Information**

Device	Package Option	BV <sub>DSS</sub> /BV <sub>DGS</sub>	$R_{\scriptscriptstyle{DS(ON)}}$	$V_{GS(th)}$	I <sub>D(ON)</sub>	
	TO-92	(V)	(max) (Ω)	(max) (V)	(min) (A)	
TP2535	TP2535N3-G	-350	25	-2.4	-0.4	

<sup>-</sup>G indicates package is RoHS compliant ('Green')

<sup>\*</sup> MIL visual screening available.





#### **Absolute Maximum Ratings**

Parameter	Value
Drain-to-source voltage	BV <sub>DSS</sub>
Drain-to-gate voltage	$BV_{DGS}$
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	+300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

#### **Pin Configuration**



## **Product Marking**



YY = Year Sealed WW = Week Sealed \_\_\_\_ = "Green" Packaging

TO-92 (N3)

<sup>\*</sup> Distance of 1.6mm from case for 10 seconds.

#### **Thermal Characteristics**

Package	I <sub>D</sub> (continuous) <sup>†</sup> (mA)	I <sub>D</sub> (pulsed) (A)	Power Dissipation @ T <sub>A</sub> = 25°C (W)	θ <sub>jc</sub> ∘c/w	θ <sub>ja</sub> °C/W	† (m <b>A</b> )	I <sub>DRM</sub> (A)
TO-92	-86	-0.6	0.74	125	170	-86	-0.6

 $<sup>\</sup>uparrow$   $I_D$  (continuous) is limited by max rated  $T_i$ .

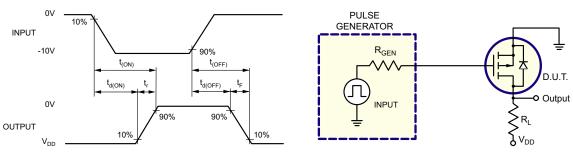
#### **Electrical Characteristics** (T<sub>A</sub> = 25°C unless otherwise specified)

Sym	Parameter	Min	Тур	Max	Units	Conditions	
BV <sub>DSS</sub>	Drain-to-source breakdown voltage	-350	-	-	V	$V_{GS} = 0V, I_{D} = -2.0 \text{mA}$	
V <sub>GS(th)</sub>	Gate threshold voltage	-1.0	-	-2.4	V	$V_{GS} = V_{DS}$ , $I_D = -1.0$ mA	
$\Delta V_{GS(th)}$	Change in V <sub>GS(th)</sub> with temperature	-	-	4.8	mV/°C	$V_{GS} = V_{DS}$ , $I_{D} = -1.0$ mA	
I <sub>GSS</sub>	Gate body leakage	-	-	-100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
			-	-10	μA	$V_{GS} = 0V, V_{DS} = Max Rating$	
I <sub>DSS</sub>	Zero gate voltage drain current	-	-	-1.0	mA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = 0V$ , $T_{A} = 125$ °C	
	On-state drain current	-0.2	-0.3	-	Α	$V_{GS} = -4.5V, V_{DS} = -25V$	
I <sub>D(ON)</sub>	On-State drain current	-0.4	-1.1	-	_ ^	$V_{GS} = -10V, V_{DS} = -25V$	
P	Static drain-to-source on-state resistance	-	20	30	Ω	$V_{GS} = -4.5V, I_{D} = -100mA$	
R <sub>DS(ON)</sub>	Static drain-to-source on-state resistance		19	25		$V_{GS} = -10V, I_{D} = -100mA$	
$\Delta R_{DS(ON)}$	Change in R <sub>DS(ON)</sub> with temperature	-	-	0.75	%/ºC	$V_{GS} = -10V, I_{D} = -100 \text{mA}$	
G <sub>FS</sub>	Forward transconductance	100	175	-	mmho	$V_{DS} = -25V, I_{D} = -100mA$	
C <sub>ISS</sub>	Input capacitance	-	60	125		V <sub>GS</sub> = 0V,	
C <sub>oss</sub>	Common source output capacitance	-	20	70	pF	$V_{DS} = -25V,$	
C <sub>RSS</sub>	Reverse transfer capacitance	-	10	25		f = 1.0 MHz	
t <sub>d(ON)</sub>	Turn-on delay time	-	-	10			
t <sub>r</sub>	Rise time	-	-	10	no	$V_{DD} = -25V,$	
t <sub>d(OFF)</sub>	Turn-off delay time		-	20	ns	$I_{D} = -0.4A,$ $R_{GEN} = 25\Omega$	
t <sub>f</sub>	Fall time	-	-	13		GEN	
V <sub>SD</sub>	Diode forward voltage drop	-	-	-1.8	V	$V_{GS} = 0V, I_{SD} = -100 \text{mA}$	
t <sub>rr</sub>	Reverse recovery time	-	300	-	ns	$V_{GS} = 0V, I_{SD} = -100 \text{mA}$	

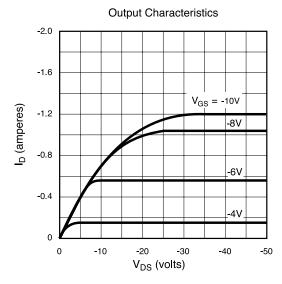
#### Notes:

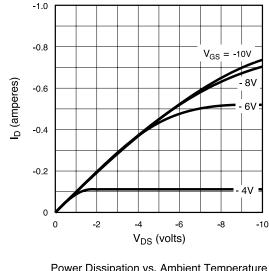
- 1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
- 2. All A.C. parameters sample tested.

## **Switching Waveforms and Test Circuit**

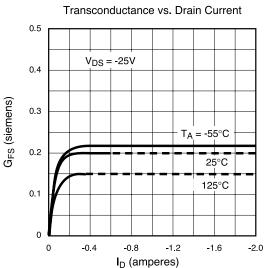


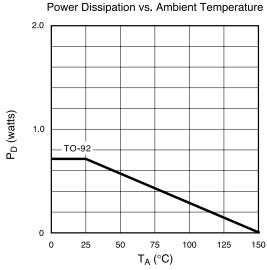
## **Typical Performance Curves**

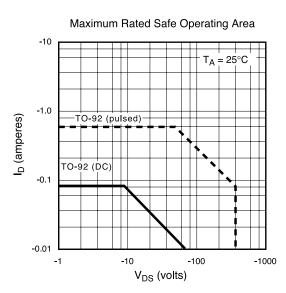


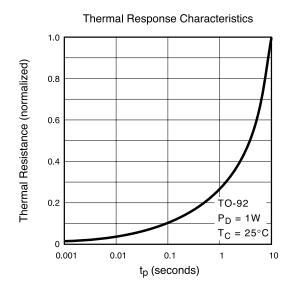


Saturation Characteristics

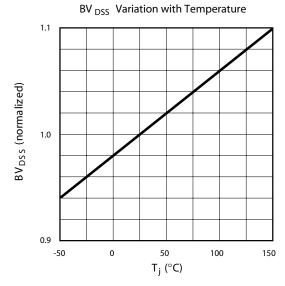


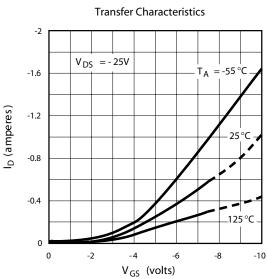


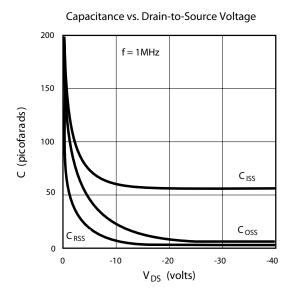


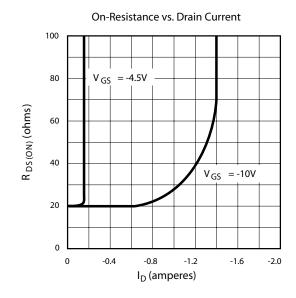


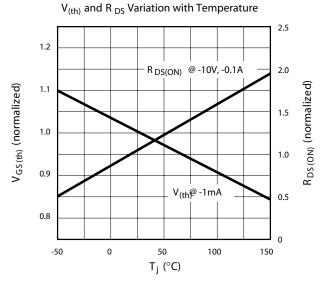
#### **Typical Performance Curves** (cont.)

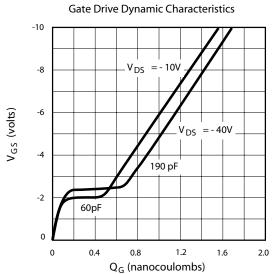




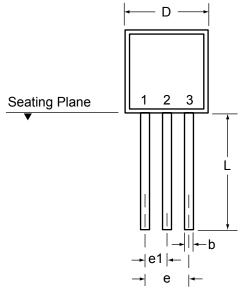


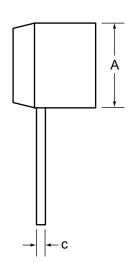






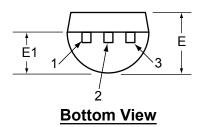
# 3-Lead TO-92 Package Outline (N3)





**Front View** 

**Side View** 



Symbol		Α	b	С	D	E	E1	е	e1	L
Dimensions (inches)	MIN	.170	.014 <sup>†</sup>	.014 <sup>†</sup>	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022 <sup>†</sup>	.022 <sup>†</sup>	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.

Drawings not to scale.

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<sup>\*</sup> This dimension is not specified in the original JEDEC drawing. The value listed is for reference only.

<sup>†</sup> This dimension is a non-JEDEC dimension.